

9.(Amended) The method of Claim 8, which further comprises: locating an interposer between the subassemblies wherein the interposer comprises dielectric layers disposed about an internal electrically conductive layer.

10.(Amended) The method of Claim 9, wherein dielectric of at least one of the surfaces that is to be bonded is from said dielectric composition.

11.(Amended) The method of Claim 8, wherein vias are disposed within each subassembly for providing electrical communication between signal planes and electrical connection to another subassembly.

12.(Amended) The method of Claim 11, wherein the vias through the signal planes are plated with a conductive metal.

13.(Amended) The method of claim 11, wherein the vias are filled with conductive adhesive.

14.(Amended) The method of Claim 9, wherein the internal electricity conductive layer of the interposer is copper.

15.(Amended) The method of Claim 9, wherein the interposer is about 3 to about 10 mils thick.

16.(Amended) The method of Claim 8, which comprises: providing top and bottom circuit layers on top and bottom external surfaces of the assembly.

17.(Amended) The method of Claim 8, wherein the laminating is carried out at about 100 to about 200°C, for about 15 minutes to about 90 minutes, and at a pressure of about 100 to about 500 psi.